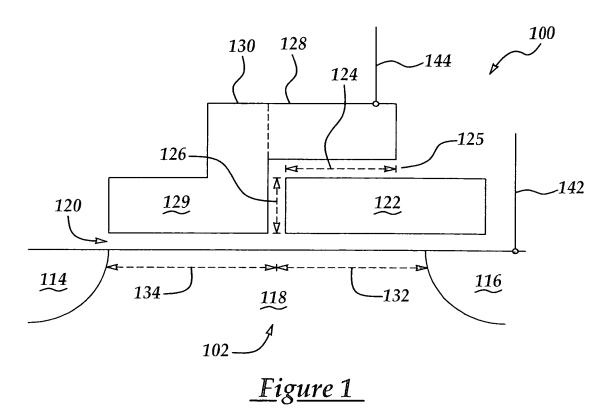
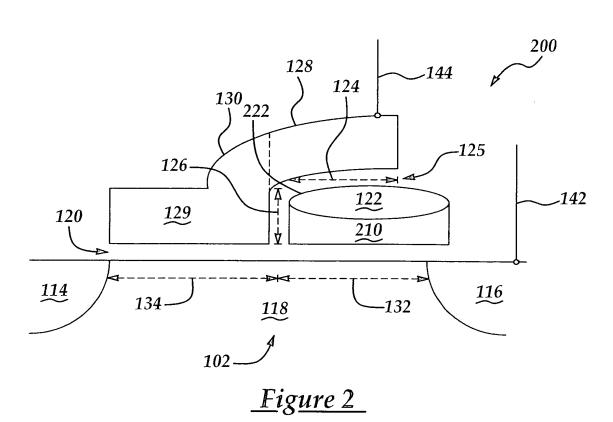
Attorney Doc. No.: 67,200-1248

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Inventor: WEN-TING CHU

Serial No.: To Be Assigned Filed: Herewith

For: A Split-Gate P-Channel Flash Memory Cell With Programming By Band-To-Band Hot Electron Method

Attorney Doc. No.: 67,200-1248

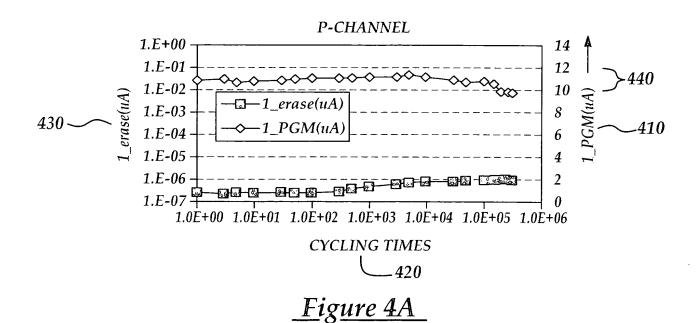


	TABLE T1 - DUAL HIGH VOLTAGE								
		CONTROL	DRAIN	SOURCE	N-WELL	PULSE			
		GATE				WIDTH			
312	PROGRAM	7.5V	-11V (UNSELECT = 0V)	OV	0V	10			
512						MICROSECS.			
314✓►	ERASE	13V	OV	0V	0V	10			
514						MILLISECS.			
316	READ	OV	1V	2.5V	2.5V				

320 ,

	TABLE T1 - DUAL HIGH VOLTAGE								
		CONTROL	DRAIN	SOURCE	N-WELL	PULSE			
		GATE				WIDTH			
322~~	PROGRAM	12.5V	0V (UNSELECT = 3V)	FLOATING	12.5V	10			
						MICROSECS.			
324✓►	ERASE	13V	0V	0V	0V	10			
3240 -						MILLISECS.			
326✓►	READ	0V	1V	2.5V	2.5V				

Figure 3



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